Attorney Docket No.: PROG2000-1C3

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of: *King*	)	Art Unit: 2815
Serial No.: *10/760,090*	)	
Filed: *01/15/04 as continuation of 10/315,741, filed 12/10/20, now U.S. patent no 6,686,631*	)	Examiner: *Unassigned*
For: *CMOS process compatible, tunable negative differential resistance (NDR) device and method of operating same*	)	

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

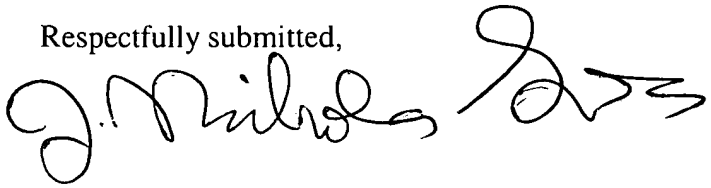
Sir:

1. Pursuant to 37 C.F.R. 1.97 and 1.98, and in compliance with 37 C.F.R. 1.56, the Office's attention is directed to the patents, publications and other information listed on the attached PTO-1449. Regarding the document(s), publication(s) or other information listed on the attached PTO-1449, Applicant believes the same may qualify as "prior" art to this application and should be treated accordingly, although Applicant(s) reserve(s) the right to contest the prior art status of any document, publication or information cited herein.

2. Pursuant to 37 C.F.R. 1.97(b) this Statement is being filed before the mailing date of a first Office action on the merits.

3. Copies of the aforementioned references were provided by the applicant and/or cited by the examiner in the related parent application to the above. Should it be necessary for the applicant to provide additional copies of any other references, please contact the undersigned.

Respectfully submitted,



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I hereby certify that the foregoing is being deposited with the U.S. Postal Service, postage prepaid, to Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450, this 23rd day of April 2004.

Information Disclosure Statement By Applicant

Substitute for form 1449/PTO

Application Number: **10/760,090**
Filing Date: **01/15/2004**
First Named Inventor: **King**
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Examiner Name: **N/A**
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Examiner Initials	Patent Number	Publication Date	Inventor Name
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